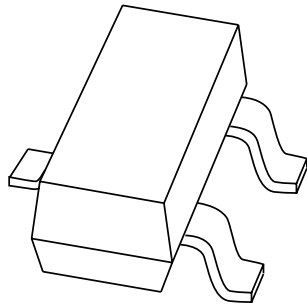


# DATA SHEET



## **BF820; BF822** NPN high-voltage transistors

Product specification  
Supersedes data of 1997 Apr 23

1999 Apr 15

NPN high-voltage transistors

BF820; BF822

FEATURES

- Low current (max. 50 mA)
- High voltage (max. 300 V).

APPLICATIONS

- Telephony and professional communication equipment.

DESCRIPTION

NPN high-voltage transistor in a SOT23 plastic package.  
PNP complements: BF821; BF823.

MARKING

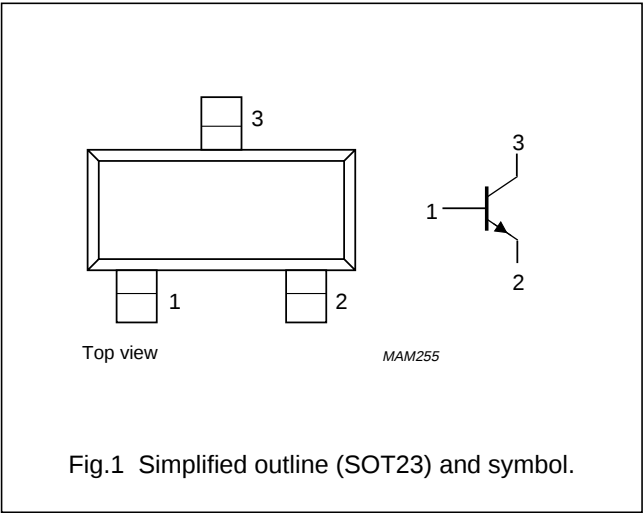
| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| BF820       | 1V*                         |
| BF822       | 1X*                         |

Note

1. \* = p : Made in Hong Kong.  
      \* = t : Made in Malaysia.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                     |      |      |      |
|                  | BF820                         |                                  | —    | 300  | V    |
|                  | BF822                         |                                  | —    | 250  | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                        |      |      |      |
|                  | BF820                         |                                  | —    | 300  | V    |
|                  | BF822                         |                                  | —    | 250  | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | —    | 5    | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | —    | 50   | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | —    | 100  | mA   |
| I <sub>BM</sub>  | peak base current             |                                  | —    | 50   | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | —    | 250  | mW   |
| T <sub>stg</sub> | storage temperature           |                                  | −65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                                  | —    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | −65  | +150 | °C   |

Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN high-voltage transistors

BF820; BF822

## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------|---------------------------------------------|------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | note 1     | 500   | K/W  |

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

| SYMBOL      | PARAMETER                            | CONDITIONS                                                     | MIN. | MAX. | UNIT          |
|-------------|--------------------------------------|----------------------------------------------------------------|------|------|---------------|
| $I_{CBO}$   | collector cut-off current            | $I_E = 0; V_{CB} = 200\text{ V}$                               | –    | 10   | nA            |
|             |                                      | $I_E = 0; V_{CB} = 200\text{ V}; T_j = 150\text{ °C}$          | –    | 10   | $\mu\text{A}$ |
| $I_{EBO}$   | emitter cut-off current              | $I_C = 0; V_{EB} = 5\text{ V}$                                 | –    | 50   | nA            |
| $h_{FE}$    | DC current gain                      | $I_C = 25\text{ mA}; V_{CE} = 20\text{ V}$                     | 50   | –    |               |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = 30\text{ mA}; I_B = 5\text{ mA}$                        | –    | 600  | mV            |
| $C_{re}$    | feedback capacitance                 | $I_C = i_c = 0; V_{CB} = 30\text{ V}; f = 1\text{ MHz}$        | –    | 1.6  | pF            |
| $f_T$       | transition frequency                 | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$ | 60   | –    | MHz           |

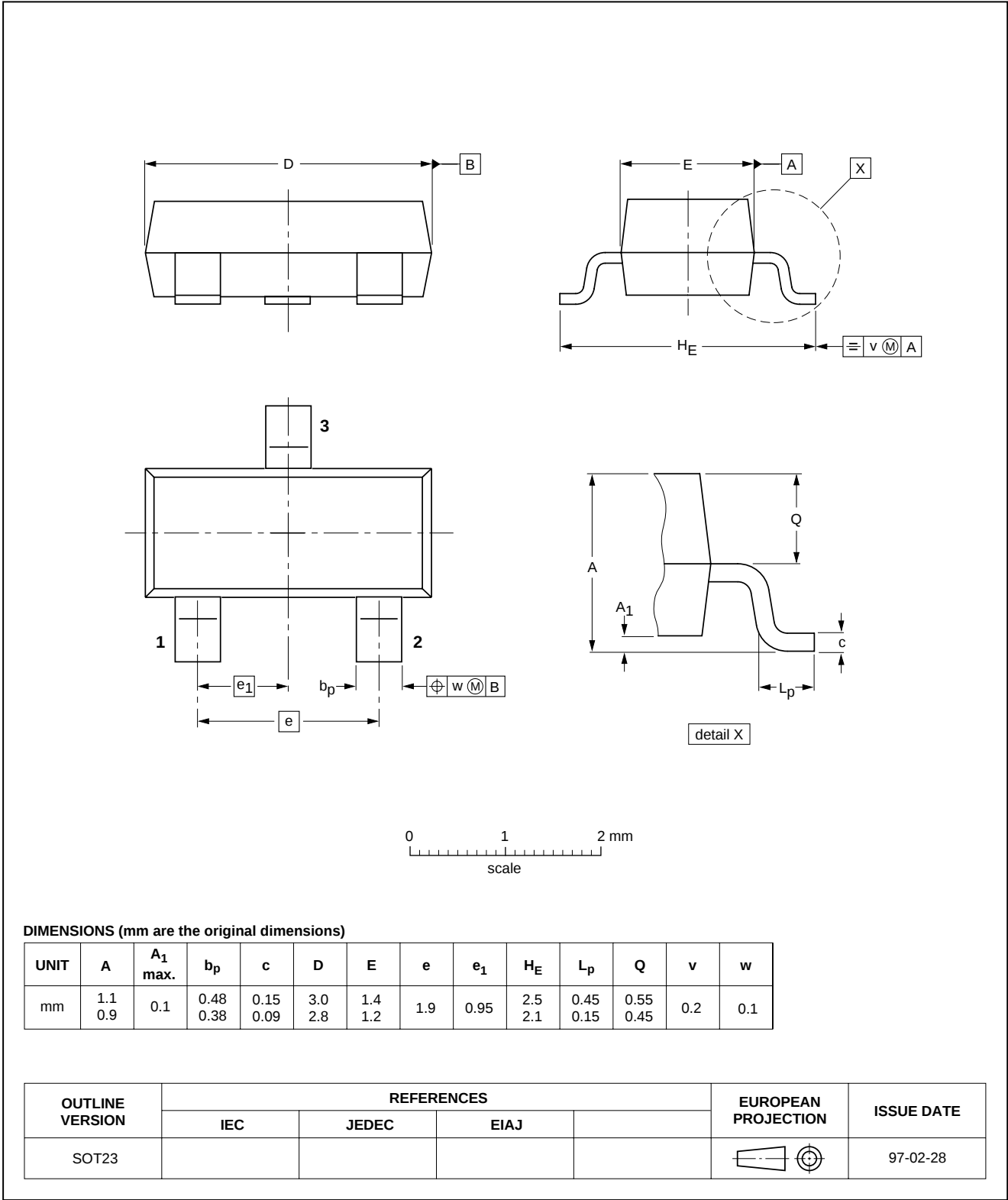
NPN high-voltage transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



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NPN high-voltage transistors

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BF820; BF822

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**DEFINITIONS**

| <b>Data sheet status</b>                                                                                                                                                                                                                                                                                                                                                                                                                                  |                                                                                       |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| Objective specification                                                                                                                                                                                                                                                                                                                                                                                                                                   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification                                                                                                                                                                                                                                                                                                                                                                                                                                 | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification                                                                                                                                                                                                                                                                                                                                                                                                                                     | This data sheet contains final product specifications.                                |
| <b>Limiting values</b>                                                                                                                                                                                                                                                                                                                                                                                                                                    |                                                                                       |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |                                                                                       |
| <b>Application information</b>                                                                                                                                                                                                                                                                                                                                                                                                                            |                                                                                       |
| Where application information is given, it is advisory and does not form part of the specification.                                                                                                                                                                                                                                                                                                                                                       |                                                                                       |

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NPN high-voltage transistors

BF820; BF822

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**NOTES**

NPN high-voltage transistors

BF820; BF822

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**NOTES**

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Printed in The Netherlands

115002/00/03/pp8

Date of release: 1999 Apr 15

Document order number: 9397 750 05657

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